

UV-A Sensor

GUVV-T13GD-L



Features

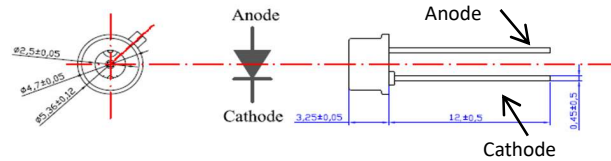
- Indium Gallium Nitride Based Material
- Schottky-type Photodiode
- Photovoltaic Mode Operation
- High Responsivity & Low Dark Current



Applications

- Full UV Band Monitoring
- UV-A Lamp Monitoring
- 365,385nm UV LED Monitoring

Outline Diagrams and Dimensions



Absolute Maximum Ratings

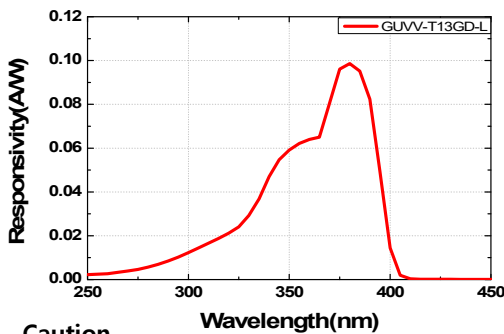
Parameter	Symbol	Min.	Max.	Unit	Remark
Storage Temperature	T_{st}	-40	90	°C	
Operating Temperature	T_{op}	-30	85	°C	
Reverse Voltage	$V_{r, max.}$		5	V	
Forward Current	$I_{f, max.}$		1	mA	
Optical Source Power Range	P_{opt}	0.01	100	mW/cm ²	UVA Lamp
Soldering Temperature	T_{sol}		260	°C	within 10 sec.

※Notice: apply to us in the case that Optical Source Power is over 100mW/cm².

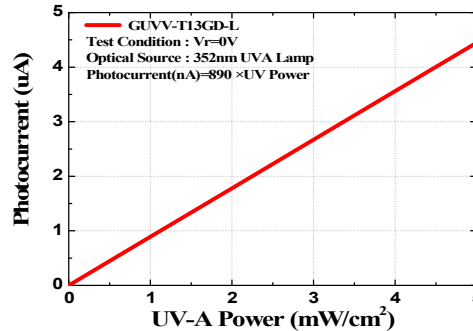
Characteristics (at 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Dark Current	I_d			20	nA	$V_r = 1\text{ V}$
Photo Current	I_{ph}	801	890	979	nA	UVA Lamp, 1mW/cm ²
Temperature Coefficient	I_{tc}		-0.03		%/°C	UVA Lamp
Responsivity	R		0.098		A/W	$\lambda = 380\text{ nm}, V_r = 0\text{ V}$
Spectral Detection Range	λ	295		400	nm	10% of R
Active area			1.024		mm ²	

Responsivity Curve



Photocurrent along UV Power



Caution

ESD can damage the device hence please avoid ESD. Insulate the cap of TO-CAN or it can cause malfunction of the device.